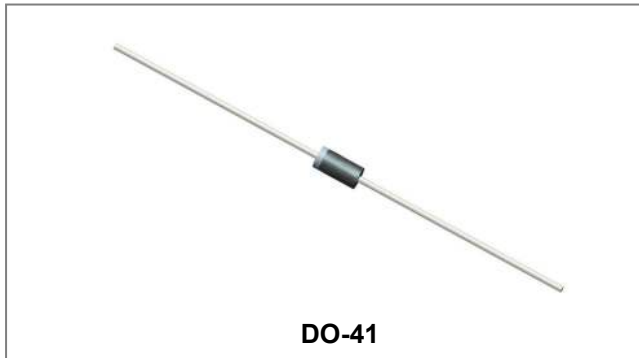


UF4001G THRU UF4007G ULTRA FAST RECTIFIERS



Features

- Super fast switching for high efficiency
- Low leakage current
- High forward surge capability
- Solder dip 260 ° C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC
- Glass Passivated Die Construction
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: JEDEC DO-41 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.33 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

	SYMBOLS	UF 4001G	UF 4002G	UF 4003G	UF 4004G	UF 4005G	UF 4006G	UF 4007G	UNIS
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current 0.375" (9.5mm) lead length at T _A =55°C	I _(AV)	1.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30.0							A
Maximum instantaneous forward voltage at 1.0A	V _F	1.0				1.70			V
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	5.0				50.0			μ A
Maximum reverse recovery time (Note 1)	t _{rr}	50				75			ns
Typical junction capacitance (Note 2)	C _J	15.0							pF
Typical thermal resistance (Note 3)	R _{CJA}	50.0							°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-65 to +150							°C

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A. Irr=0.25A
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. Thermal resistance from junction to ambient at 0.375"(9.5mm) lead length, P.C.B mounted.

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Ratings and Characteristics Curves

FIG. 1- FORWARD CURRENT DERATING CURVE

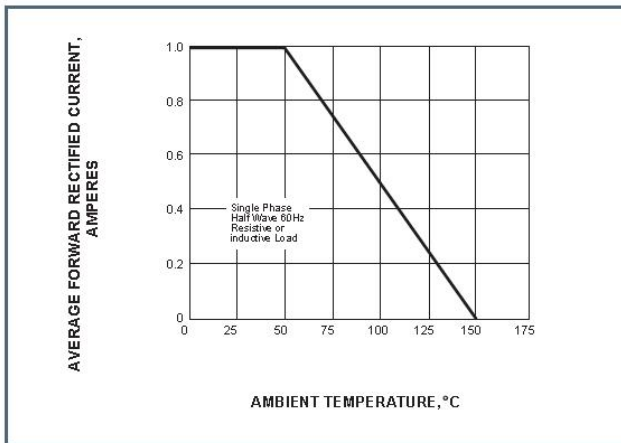


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

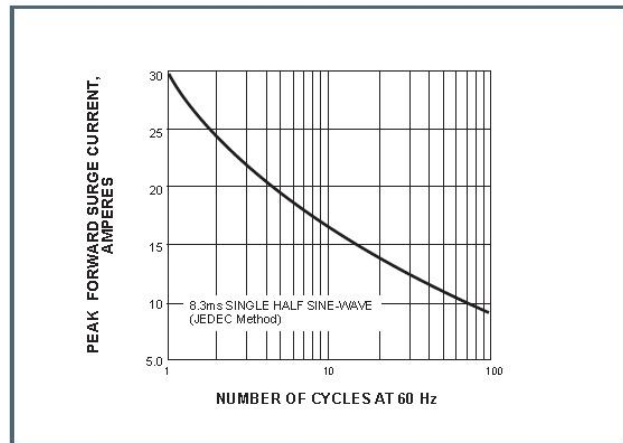


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

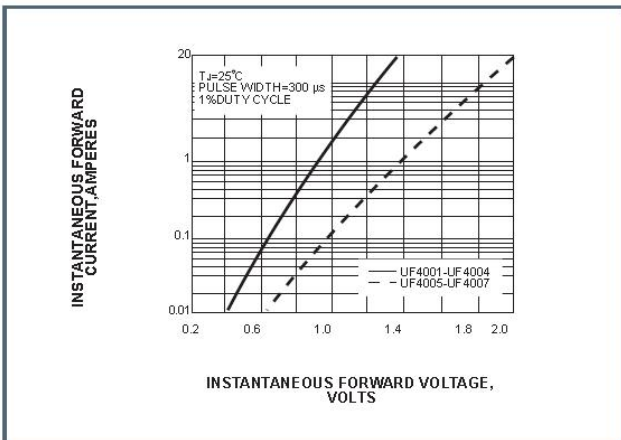
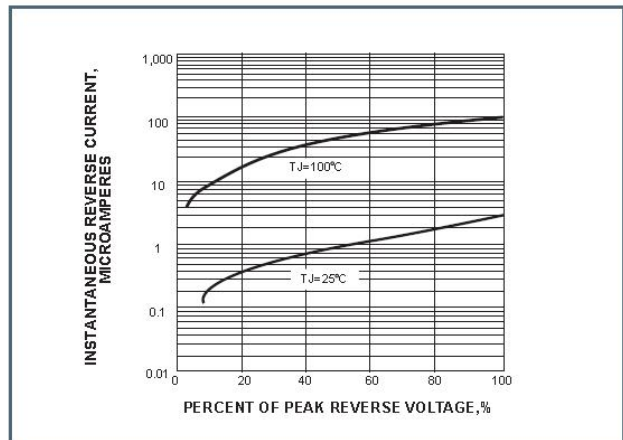
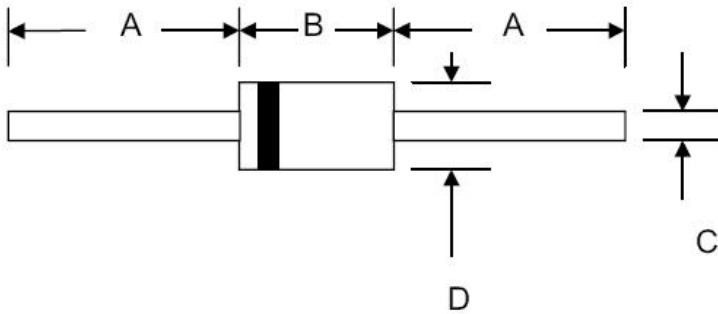


FIG. 4-TYPICAL REVERSE CHARACTERISTICS



Mechanical Dimensions DO-41



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	4.06	5.21	0.160	0.205
C	0.71	0.864	0.028	0.034
D	2.00	2.72	0.079	0.107

Ordering Information

Device	Package	Shipping
UF4001G THRU UF4007G	DO-41 (Pb-Free)	5000pcs /Tape

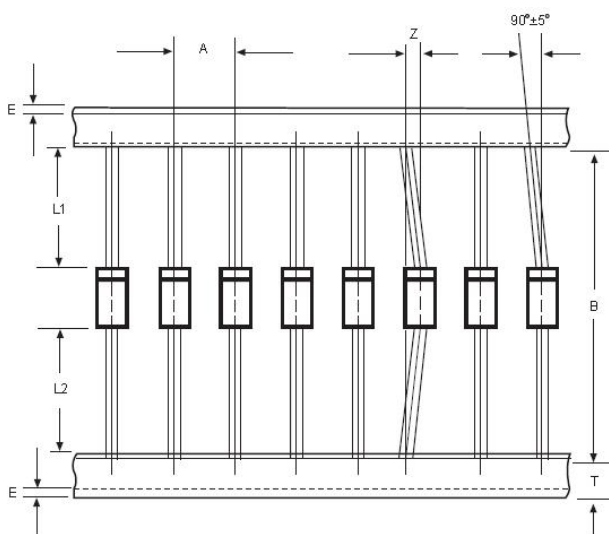
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



UF4001G = Part Name

Carrier Tape Specification DO-41



SYMBOL	Millimeters	
	Min.	Max.
A	4.50	5.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

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